

A REPLACEMENT GATE STRAINED SILICON FINFET PROCESS

ABSTRACT OF THE DISCLOSURE

An exemplary embodiment relates to a method of FinFET formation. The method can include providing a sacrificial fin structure,
5 removing the sacrificial fin structure, and providing a strained silicon layer at the location of the removed sacrificial gate structure. The FinFET can include a strained-Si MOSFET channel region.